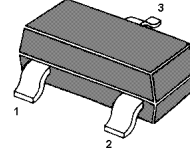
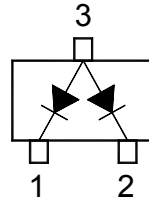


SDB720S

SILICON EPITAXIAL PLANAR DIODE SCHOTTKY BARRIER DIODE

for high speed switching circuit and small
current rectification applications



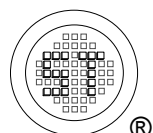
Marking Code: **FZ**
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	30	V
Reverse Voltage	V_R	30	V
Non-repetitive Peak Surge Current	I_{FSM}	1	A
Average Forward Current	I_O	200	mA
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	V_F	-	-	0.55	V
Reverse Current at $V_R = 30\text{ V}$	I_R	-	-	50	μA
Total Capacitance at $V_R = 0, f = 1\text{ MHz}$	C_T	-	30	-	pF
Reverse Recovery Time at $I_R = I_F = 10\text{ mA}$	t_{rr}	-	3	-	ns



Dated : 18/12/2005

